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INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification 6 : H01L 21/28, 21/324 — A1

(11) International Publication Number: **WO 99/40615**

(43) International Publication Date: 12 August 1999 (12.08.99)

(21) International Application Number: PCT/US99/02504

(22) International Filing Date: 4 February 1999 (04.02.99)

(30) Priority Data:

09/018,783	4 February 1998 (04.02.98)	US
60/087,432	1 June 1998 (01.06.98)	US

(81) Designated States: CN, GD, IN, JP, KR, SG, US, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).

Published
With international search report.
Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.

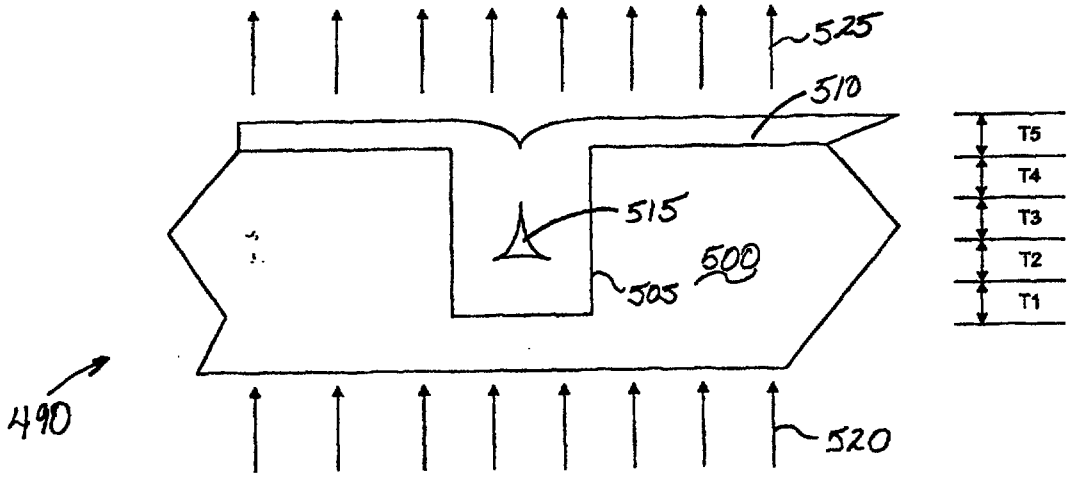
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(54) Title: METHOD AND APPARATUS FOR LOW-TEMPERATURE ANNEALING OF METALLIZATION MICRO-STRUCTURES IN THE PRODUCTION OF A MICROELECTRONIC DEVICE



(57) Abstract

A method for filling recessed micro-structures (505) at a surface of a microelectronic workpiece (500), such as a semiconductor wafer, with metallization is set forth. In accordance with the method, a metal layer is deposited into the micro-structures with a process, such as an electroplating process, that generates metal grains that are sufficiently small so as to substantially fill the recessed micro-structures. The deposited metal is subsequently subjected to an annealing process at a temperature below about 100 degrees Celsius, and may even take place at ambient room temperature to allow grain growth which provides optimal electrical properties. Various novel apparatus for executing unique annealing processes are also set forth.